

1.Cathode

2 Anode

SDURF3030CTR

3.Cathode

Technical Data Data Sheet N1083, Rev. -

Green Products

SDURF3030CT/CTR ULTRAFAST PLASTIC RECTIFIER

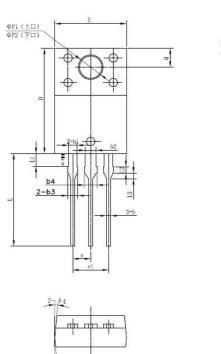
Applications:

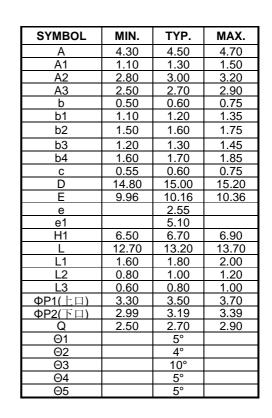
- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Features:

- Fully Molded Isolation
- Dual Diodes-Cathode Common
- Ultra-Fast Recovery
- Low Forward Voltage Drop
- High Surge Capability
- 200 Volts thru 600 Volts Types Available
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm





SDURF3030CT

ITO-220AB

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FAX (86) 25-87123900 • World Wide Web Site - http://www.sangdest.com.cn • E-Mail Address - sales@ sangdest.com.cn •

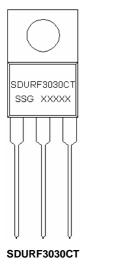


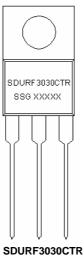
Data Sheet N1083, Rev. -

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Marking Diagram:

Technical Data





Where XXXXX is YYWWL

SDUR	= Device Type
F	= Package Type
30	= Forward Current (30A)
30	= Reverse Voltage (300V)
CT/CTR	= Configuration
SSG	= SSG
ΥY	= Year
WW	= Week
L	= Lot Number

Ordering Information:

Device	Package	Shipping	
SDURF3030CT/CTR	ITO-220AB	50pcs / tube	
SDURFSUSUEI/GTR	(Pb-Free)	Sopes / tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	300	V
Average Rectified Forward Current	I _{F (AV)}	Rated Vr ,@Tc=105℃	30	А
Max. Peak One Cycle Non- Repetitive Surge Current (Per leg)	I _{FSM}	8.3ms, Half Sine pulse	110	А



Technical Data Data Sheet N1083, Rev. -

Green Products

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop*	V _{F1}	@ 15A, Pulse, T _J = 25°C	1.25	V
Max. Reverse Current*	I _{R1}	$@V_R = rated V_R$ T _J = 25°C	10	μA
	I _{R2}	$@V_R = rated V_R$ T _J = 125°C	1.0	mA
Max. Reverse Recovery Time	t _{rr}	I_F =500mA, I_R =1A, and I_{rm} =250mA	45	ns

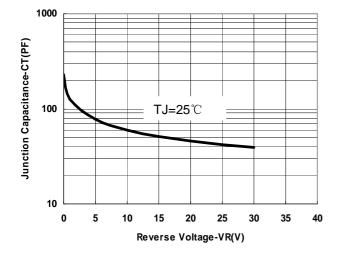
 $^{*}\,$ Pulse width < 300 $\mu s,\,$ duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	TJ	-	-55 to +150	°C
Max. Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case	$R_{ ext{ heta}JC}$	DC operation	1.75	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			



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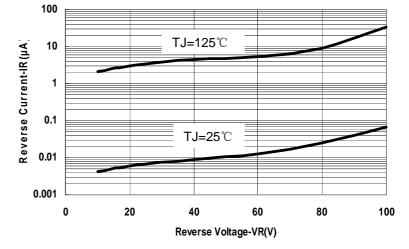


Fig.1-Typical Junction Capacitance Vs.Reverse Voltage

Fig.2-Typical Values Of Reverse Current VS.Reverse Voltage

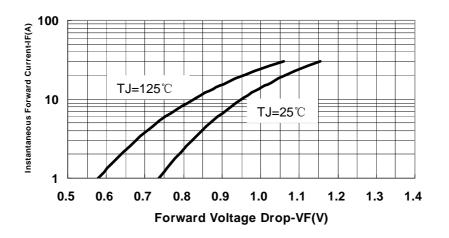


Fig.3-Typical Forward Voltage Drop Characteristics



Technical Data Data Sheet N1083, Rev. -

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